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KOREAN PATENT ABSTRACTS

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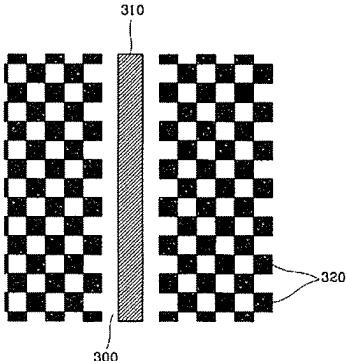
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(51)Int. Cl

H01L 21 /027**(54) MASK FOR MODIFYING OPTICAL PROXIMITY EFFECT AND FABRICATING METHOD THEREOF**

(57) Abstract:

PURPOSE: A mask for modifying an optical proximity effect(OPC) is provided to improve a whole focus margin, by making diffraction light of an isolated pattern have a diffraction type of diffraction light of a dense pattern. CONSTITUTION: A main pattern(310) has a light characteristic opposite to that of a mask substrate(300), formed on the mask substrate. A plurality of dummy phase shifters(320) change the phase of transmitted exposure light, formed on the mask substrate at both sides of the main pattern. A mask includes the main pattern and the plurality of phase shifters.



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